

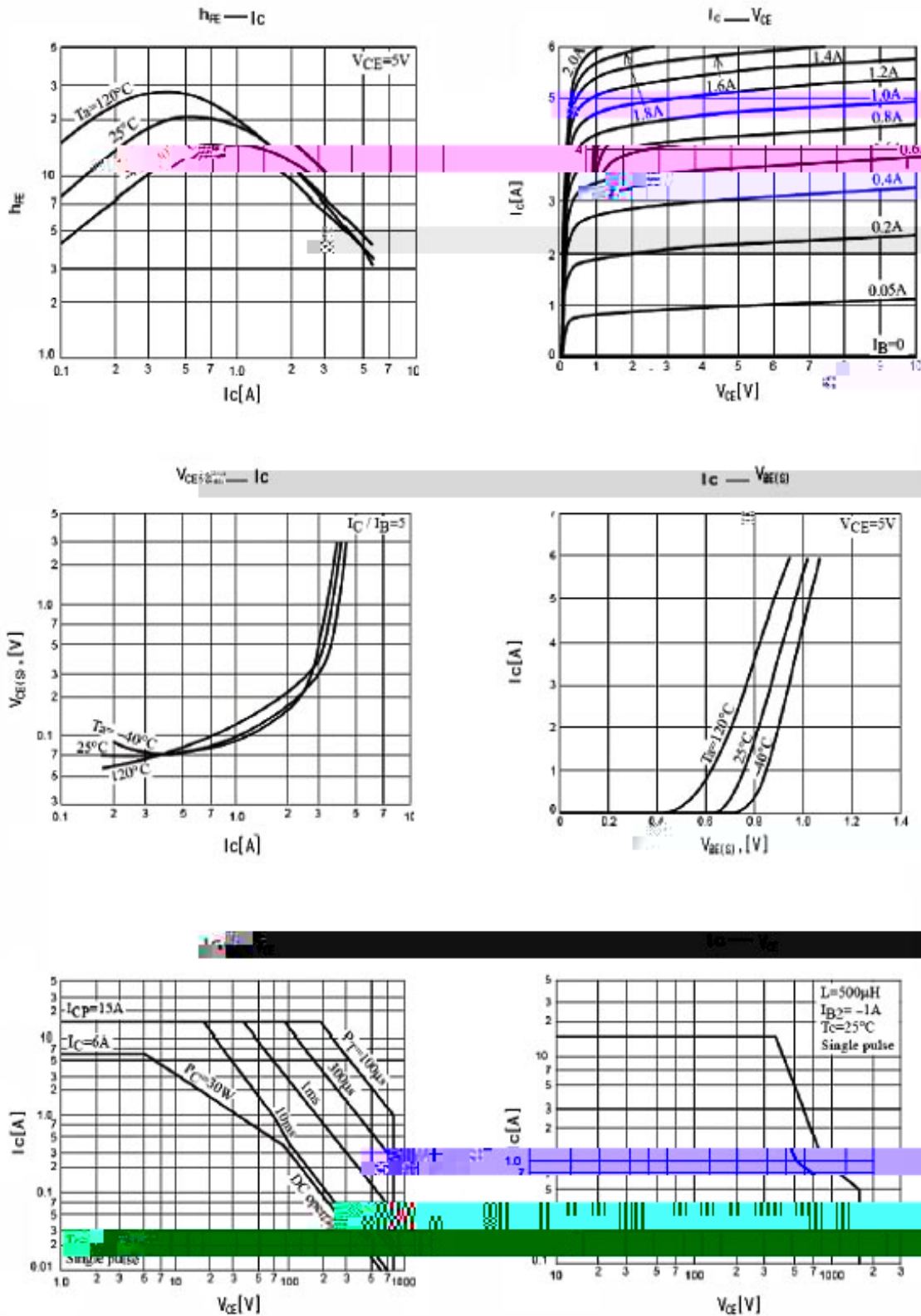
TR0550F QSQ Ⅱ 1 Silicon NPN transistor in a TO-220F Plastic Package.

高耐压、宽SOA、高速开关、低饱和压降、优良的电流特性、内置阻尼二极管。
High breakdown voltage, Wide SOA, High switching speed, Low saturation voltage, Excellent current characteristics, Bulit-in dumper diode.

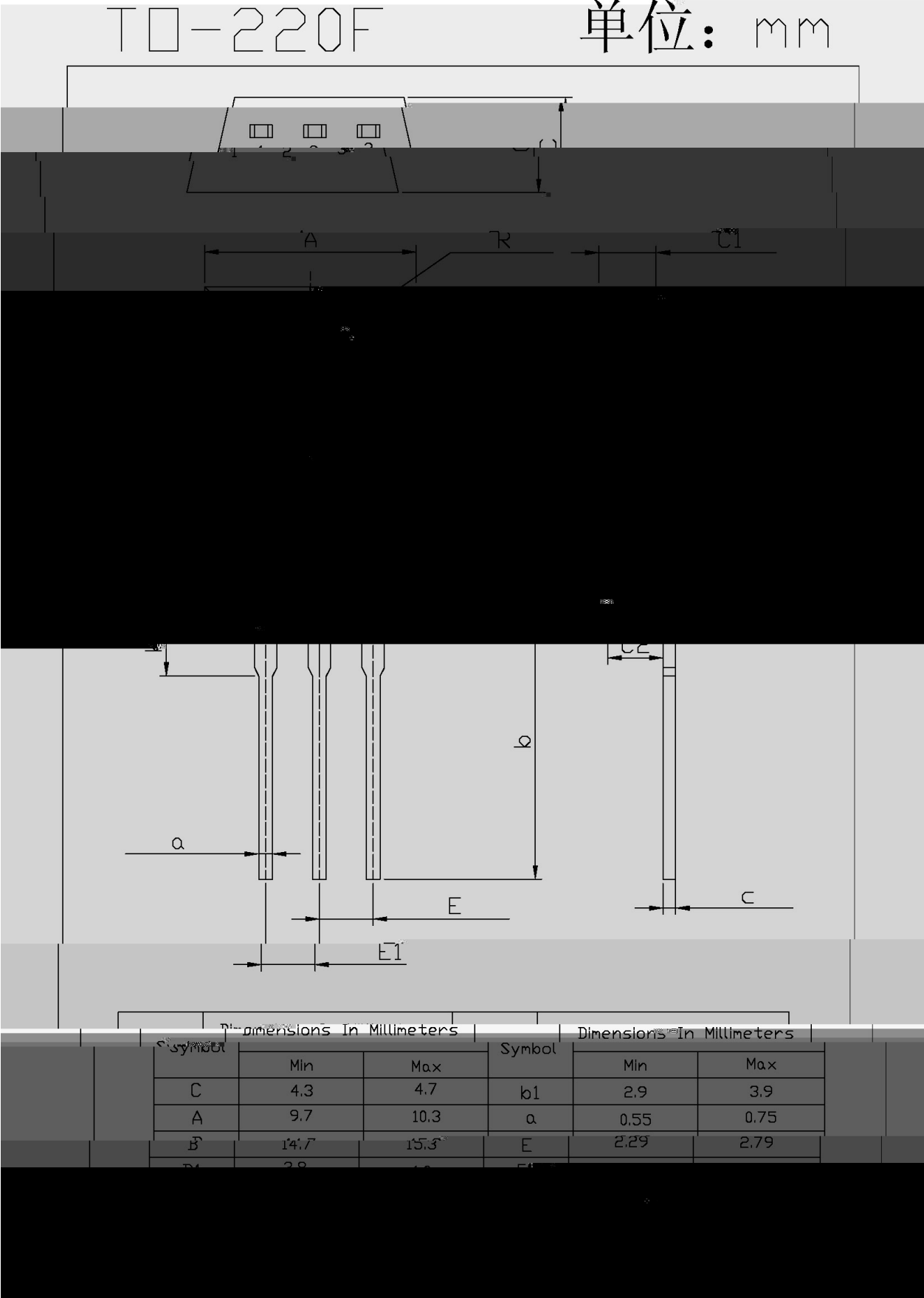
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	1500	V
Collector to Emitter Voltage($V_{BE}=0$)	V_{CES}	1500	V
Collector to Emitter Voltage	V_{CEO}	800	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	6.0	A
Peak Collector Current	I_{CP}	15.0	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C(T_c=25^\circ C)$	30	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=500mA$ $I_C=0$	5.0			V
Forward Voltage	V_F	$I_F=3A$			2.0	V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=1000V$ $I_E=0$			50	μA
		$V_{CB}=1500V$ $I_E=0$			1.0	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=4V$ $I_C=0$	40		130	mA
DC Current Gain*	h_{FE}^*	$V_{CE}=5.0V$ $I_C=3.0A$	5		10	
Collector to Emitter Saturation Voltage*	$V_{CE(sat)}$					

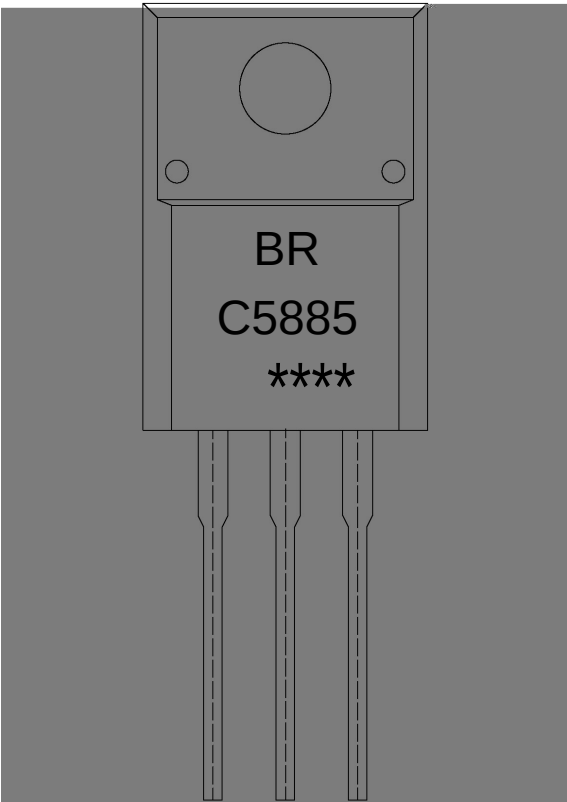
/ Electrical Characteristic Curve



/ Package Dimensions

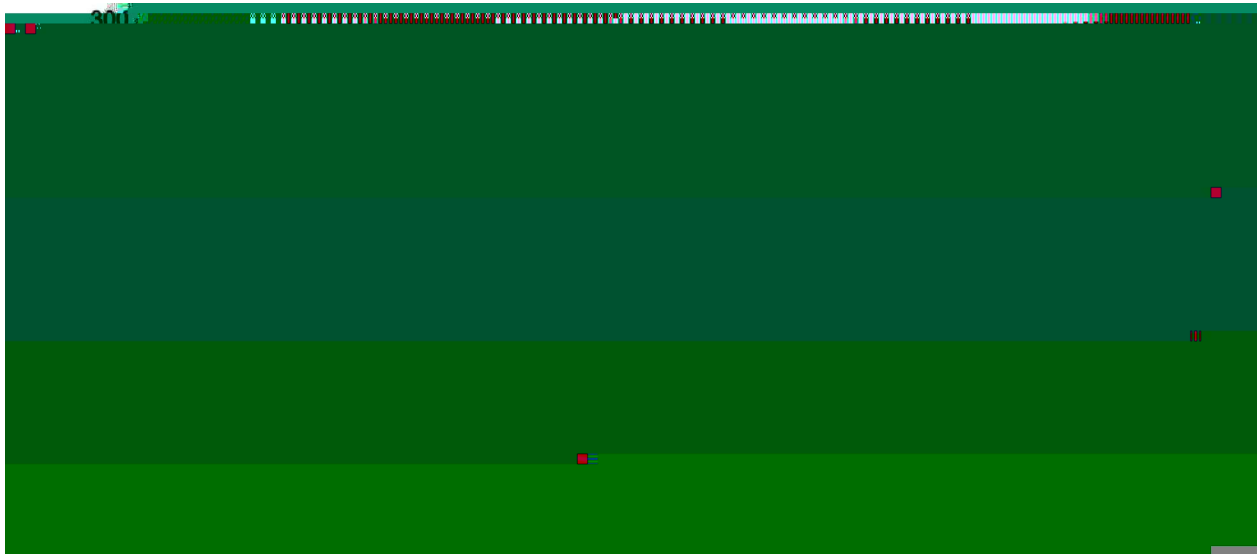


/ Marking Instructions



ER	公司代码
F5885	产品型号
****	批次号
Note:	
BR:	Company Code
C5885:	Product Type.
****:	Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



- Note:
1. Preheating: 25~150 °C, Time: 60~90sec;
 2. Peak Temp.: 255±5 °C, Duration: 5±0.5sec;
 3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Heat Test Conditions

□ 270±5 °C, Time: 10±1 sec. Temp.: 270±5 °C Time: 10±1 sec

/ Packaging SPEC.

□ / BULK

Package Type 封装形式	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Units 包装数量	Dimension 包装尺寸 (unit: mm ³)
				6000	